

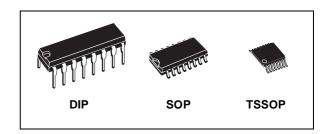
4-BIT MAGNITUDE COMPARATOR

- HIGH SPEED : t_{PD} = 20 ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION: $I_{CC} = 4\mu A(MAX.)$ at $T_A = 25$ °C
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 85



The M74HC85 is an high speed CMOS 4-BIT MAGNITUDE COMPARATOR fabricated with silicon gate C²MOS technology.

This comparator compares two 4-bit words and provides an high voltage level on one of the A>B out, A=B out and A<B out outputs. The comparing



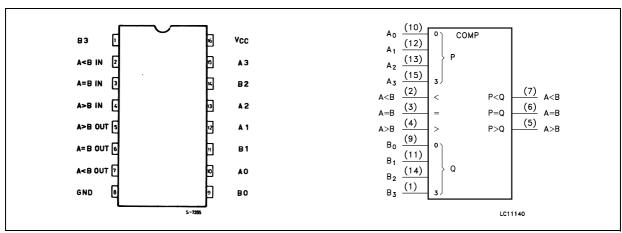
ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC85B1R	
SOP	M74HC85M1R	M74HC85RM13TR
TSSOP		M74HC85TTR

bit number is easily expanded by cascading several devices as shown in the typical application.

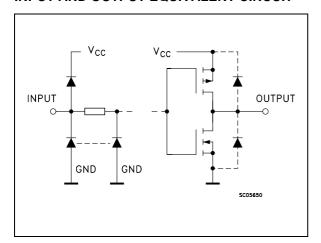
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/10

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

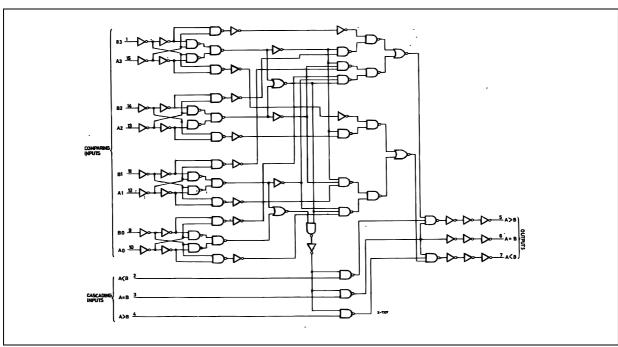
PIN No	SYMBOL	NAME AND FUNCTION
2	IN _{A<b< sub=""></b<>}	A <b expansion="" input<="" td="">
3	$IN_{A=B}$	A=B Expansion Input
4	IN _{A>B}	A>B Expansion Input
5	OUT _{A>B}	A>B Expansion Output
6	$OUT_{A=B}$	A=B Expansion Output
7	OUT _{A<b< sub=""></b<>}	A <b expansion="" output<="" td="">
9, 11, 14, 1	B ₀ to B ₃	Word B Inputs
10, 12, 13, 15	A_0 to A_3	Word A Inputs
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

TRUTH TABLE

	COMPARIN	IC INDUTE		CASC	ADING II	NPUTS	OUTPUTS		
	COMPARI	NG INPUIS		A>B	A <b< th=""><th>A=B</th><th>A>B</th><th>A<b< th=""><th>A=B</th></b<></th></b<>	A=B	A>B	A <b< th=""><th>A=B</th></b<>	A=B
A3 > B3	X	Х	X	Х	Х	Х	Н	L	L
A3 = B3	A2 > B2	Х	Х	Х	Х	Х	Н	L	L
A3 = B3	A2 = B2	A1 > B1	Х	Х	Х	Х	Н	L	L
A3 = B3	A2 = B2	A1 = B1	A0 > B0	Х	Х	Х	Н	L	L
		A1 = B1	A0 = B0	L	L	L	Н	Н	L
				Х	Х	Н	L	L	Н
A3 = B3	A2 = B2			L	Н	L	L	Н	L
				Н	L	L	Н	L	L
				Н	Н	L	L	L	L
A3 = B3	A2 = B2	A1 = B1	A0 < B0	Х	X	X	L	Н	L
A3 = B3	A2 = B2	A1 > B1	Х	Х	Х	Х	L	Н	L
A3 = B3	A2 < B2	Х	Х	Х	Х	Х	L	Н	L
A3 < B3	Х	Х	Х	Х	Х	Х	L	Н	L

X : Don't Care

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage	2 to 6	V	
V _I	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage	0 to V _{CC}	V	
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000	ns
t_r , t_f		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

DC SPECIFICATIONS

		1	est Condition	Value							
Symbol	Parameter	V _{CC}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V _{OH} High Level Output	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9			
	Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

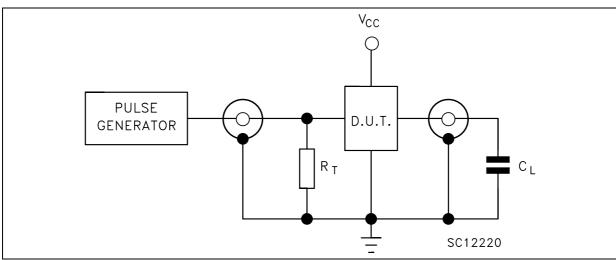
		٦	Test Condition	Value							
Symbol Parameter		V _{CC} (V)	T _A = 25°C			-40 to	85°C	-55 to 125°C		Unit	
	Min.		Тур.	Max.	Min.	Max.	Min.	Max.			
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110	
	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay	2.0			96	185		230		280	
	Time (A, B-OUT)	4.5			24	37		46		56	ns
		6.0			20	31		39		48	
t _{PLH} t _{PHL}	Time	2.0			48	95		120		145	
		4.5			12	19		24		29	ns
	(CASCADE-OUT)	6.0			10	16		20		25	

CAPACITIVE CHARACTERISTICS

		Test Condition		Value							
Symbol	ol Parameter V _{CC}			T _A = 25°C		-40 to 85°C -5		-55 to	-55 to 125°C		
	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			23						pF

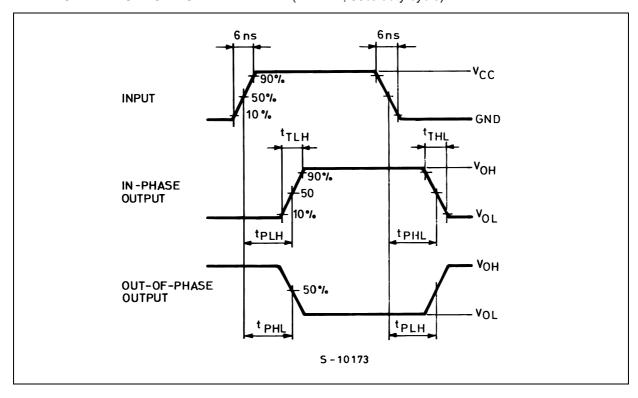
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} x V_{CC} x f_{IN} + I_{CC}

TEST CIRCUIT



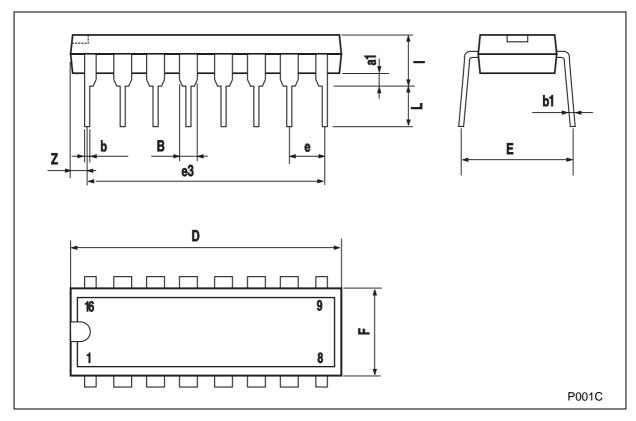
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



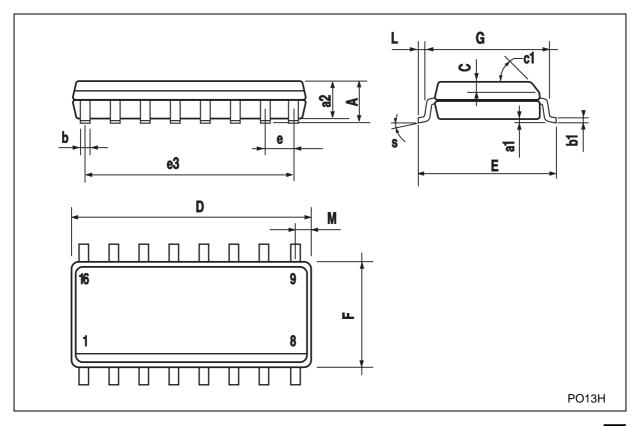
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



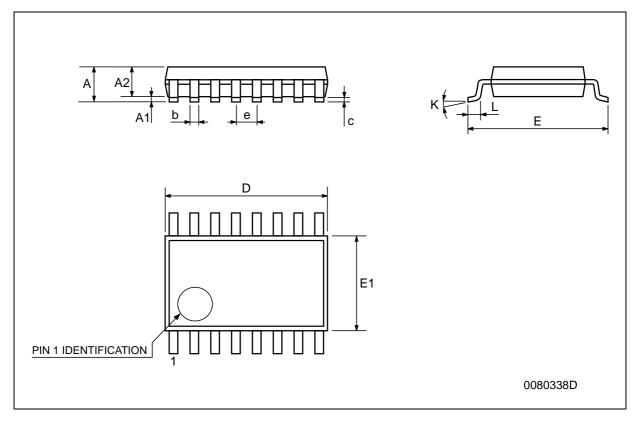
SO-16 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)	•	
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
еЗ		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (max.)	·	



TSSOP16 MECHANICAL DATA

DIM.		mm.		inch				
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



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